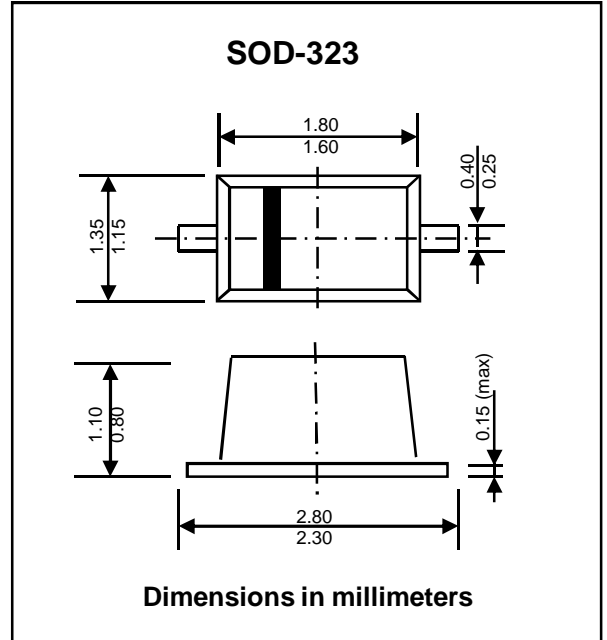


1N119WS

SILICON EPITAXIAL PLANAR DIODE



APPLICATIONS

- High speed switching

MECHANICAL DATA :

- Case : SOD-323
- Marking Code : " W2 "

Absolute Maximum Ratings (Ta = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Average Forward Current	I_O	100	mA
Peak Forward Current	I_{FM}	300	mA
Non-repetitive Peak Forward Current (t = 1μs)	I_{FSM}	4	A
Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{stg}	-55 to + 125	°C

ELECTRICAL CHARACTERISTICS (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage	$I_F = 10 \text{ mA}$	V_F	-	-	0.8	V
	$I_F = 100 \text{ mA}$	V_F	-	-	1.2	V
Reverse Current	$V_R = 80 \text{ V}$	I_R	-	-	0.1	μA
Capacitance between Terminals	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_T	-	-	2	pF
Reverse Recovery Time	$V_R = 6 \text{ V}, I_F = 10 \text{ mA}, R_L = 50 \Omega$	T_{rr}	-	-	3	ns

RATING AND CHARACTERISTIC CURVES (1N119WS)

FIG.1 - FORWARD CURRENT VS. FORWARD VOLTAGE

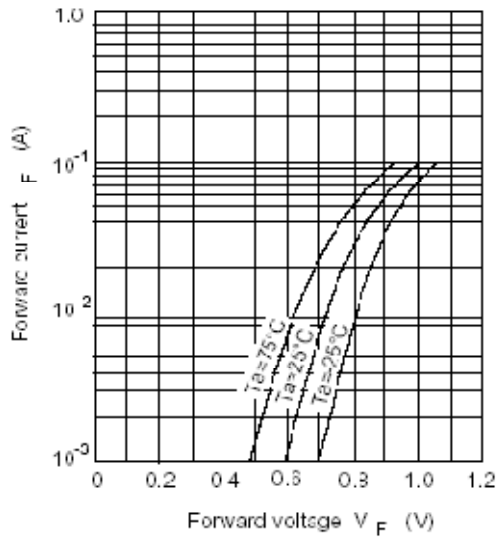


FIG.2 - REVERSE CURRENT VS. REVERSE VOLTAGE

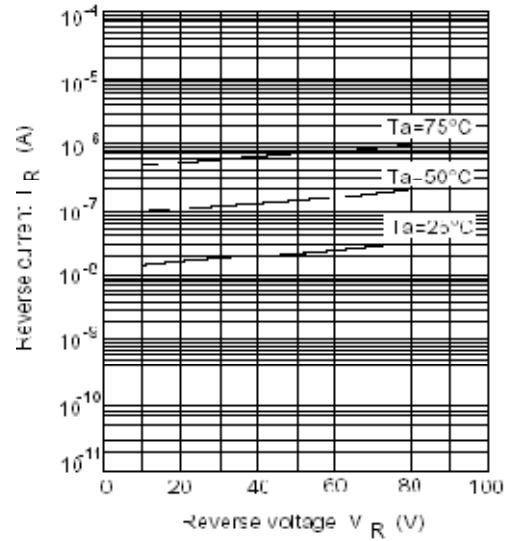


FIG.3 - CAPACITANCE VS. REVERSE VOLTAGE

